

isc Silicon NPN Power Transistors

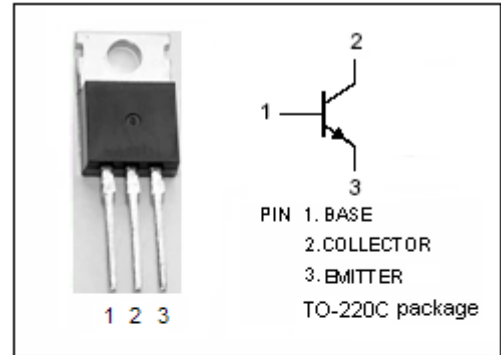
2SC3549

DESCRIPTION

- High Voltage
- High Speed Switching
- High Reliability

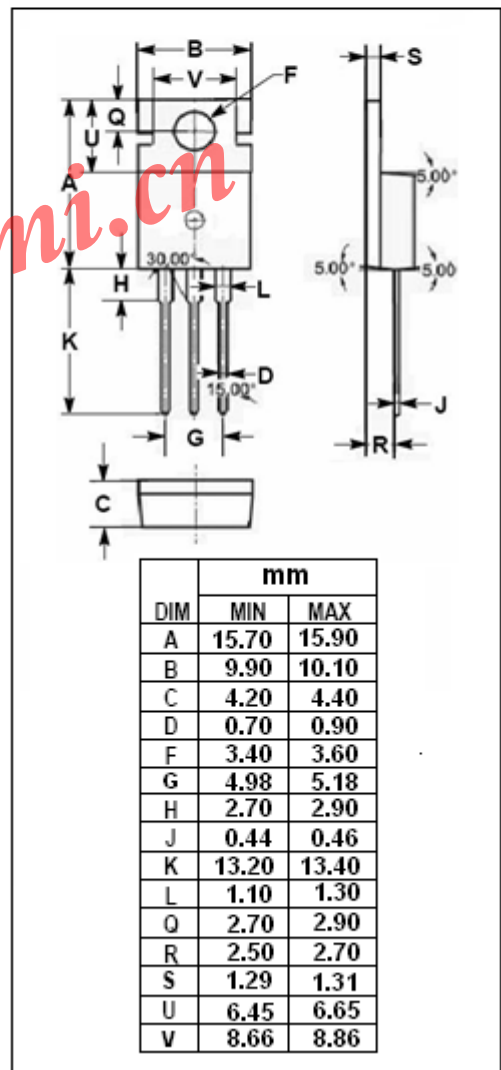
APPLICATIONS

- Switching regulators
- DC-DC converter
- Solids state relay
- General purpose power amplifiers



ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	900	V
V _{CEO}	Collector-Emitter Voltage	800	V
V _{EBO}	Emitter-Base Voltage	10	V
I _C	Collector Current-Continuous	3	A
I _B	Base Current-Continuous	1	A
P _C	Collector Power Dissipation @ T _C =25°C	40	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55~150	°C



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	4.16	°C/W

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ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=10\text{mA}; I_B=0$	800			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=1\text{mA}; I_E=0$	900			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=1\text{mA}; I_C=0$	10			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=1\text{A}; I_B=0.2\text{A}$			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=1\text{A}; I_B=0.2\text{A}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=900\text{V}; I_E=0$			1.0	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=10\text{V}; I_C=0$			1.0	mA
h_{FE}	DC Current Gain	$I_C=1\text{A}; V_{CE}=5\text{V}$	10			

Switching times

t_{on}	Turn-on Time	$I_C=2\text{A}; I_{B1}=0.4\text{A}; I_{B2}=-0.8\text{A}$ $R_L=150\Omega$; $P_W=20\mu\text{s}; \text{Duty}\leq 2\%$			1.0	μs
t_{stg}	Storage Time				4.0	μs
t_f	Fall Time				0.8	μs